Peter Krogstrup

List of Publications by Year in Descending Order

46 papers	2,528 citations	22 h-index	48 g-index
48 ext. papers	2,910 ext. citations	9.7 avg, IF	4.64 L-index

#	Paper	IF	Citations
46	Signatures of Andreev Blockade in a Double Quantum Dot Coupled to a Superconductor.. *Physical Review Letters*, **2022**, 128, 046801	7.4	1
45	Andreev Interference in the Surface Accumulation Layer of Half-Shell InAsSb/Al Hybrid Nanowires.. *Advanced Materials*, **2022**, e2108878	24	2
44	Enhancing the NIR Photocurrent in Single GaAs Nanowires with Radial p-i-n Junctions by Uniaxial Strain. *Nano Letters*, **2021**, 21, 9038-9043	11.5	3
43	Band Structure Extraction at Hybrid Narrow-Gap Semiconductor-Metal Interfaces. *Advanced Science* , **2021**, 8, 2003087	13.6	6
42	Multiterminal Quantized Conductance in InSb Nanocrosses. *Advanced Materials*, **2021**, 33, e2100078	24	1
41	Highly Transparent Gatable Superconducting Shadow Junctions. *ACS Nano*, **2020**, 14, 14605-14615	16.7	16
40	Coherent Epitaxial Semiconductor-Ferromagnetic Insulator InAs/EuS Interfaces: Band Alignment and Magnetic Structure. *ACS Applied Materials & Interfaces*, **2020**, 12, 8780-8787	9.5	10
39	Semiconductor-Ferromagnetic Insulator-Superconductor Nanowires: Stray Field and Exchange Field. *Nano Letters*, **2020**, 20, 456-462	11.5	16
38	The Effect of Bending Deformation on Charge Transport and Electron Effective Mass of p-doped GaAs Nanowires. *Physica Status Solidi - Rapid Research Letters*, **2019**, 13, 1900134	2.5	6
37	Superconducting vanadium/indium-arsenide hybrid nanowires. *Nanotechnology*, **2019**, 30, 294005	3.4	15
36	The Effect of Bending Deformation on Charge Transport and Electron Effective Mass of p-doped GaAs Nanowires. *Physica Status Solidi - Rapid Research Letters*, **2019**, 13, 1970033	2.5	
35	Selective-area chemical beam epitaxy of in-plane InAs one-dimensional channels grown on InP(001), InP(111)B, and InP(011) surfaces. *Physical Review Materials*, **2019**, 3,	3.2	26
34	Selectivity Map for Molecular Beam Epitaxy of Advanced III-V Quantum Nanowire Networks. *Nano Letters*, **2019**, 19, 218-227	11.5	51
33	Correlation between Electrical Transport and Nanoscale Strain in InAs/InGaAs Core-Shell Nanowires. *Nano Letters*, **2018**, 18, 4949-4956	11.5	12
32	An STM SEM setup for characterizing photon and electron induced effects in single photovoltaic nanowires. *Nano Energy*, **2018**, 53, 175-181	17.1	4
31	Au-Assisted Substrate-Faceting for Inclined Nanowire Growth. *Nano Letters*, **2018**, 18, 4115-4122	11.5	3
30	Engineering hybrid epitaxial InAsSb/Al nanowires for stronger topological protection. *Physical Review Materials*, **2018**, 2,	3.2	50

29	Field effect enhancement in buffered quantum nanowire networks. *Physical Review Materials*, **2018**, 2,	3.2	44
28	Surface optical phonon propagation in defect modulated nanowires. *Journal of Applied Physics*, **2017**, 121, 085702	2.5	2
27	Scaling of Majorana Zero-Bias Conductance Peaks. *Physical Review Letters*, **2017**, 119, 136803	7.4	221
26	Epitaxy of advanced nanowire quantum devices. *Nature*, **2017**, 548, 434-438	50.4	192
25	Growth of InAs Wurtzite Nanocrosses from Hexagonal and Cubic Basis. *Nano Letters*, **2017**, 17, 6090-6096	11.5	22
24	Atomic Scale Characterization on III-V Based Heterostructure Nanowire Interfaces **2016**, 544-545		
23	Nanowire-Aperture Probe: Local Enhanced Fluorescence Detection for the Investigation of Live Cells at the Nanoscale. *ACS Photonics*, **2016**, 3, 1208-1216	6.3	17
22	Morphology and composition of oxidized InAs nanowires studied by combined Raman spectroscopy and transmission electron microscopy. *Nanotechnology*, **2016**, 27, 305704	3.4	16
21	Ag-catalyzed InAs nanowires grown on transferable graphite flakes. *Nanotechnology*, **2016**, 27, 365603	3.4	12
20	Topological Phases in InAs_{1-x}Sb_{x}: From Novel Topological Semimetal to Majorana Wire. *Physical Review Letters*, **2016**, 117, 076403	7.4	76
19	Vapour-liquid-solid growth: Nanowire-quantum dot epitaxy. *Nature Materials*, **2015**, 14, 757-9	27	3
18	Modulation of fluorescence signals from biomolecules along nanowires due to interaction of light with oriented nanostructures. *Nano Letters*, **2015**, 15, 176-81	11.5	16
17	Advances in the theory of III–V nanowire growth dynamics. *Journal Physics D: Applied Physics*, **2013**, 46, 313001	3	102
16	Surface-passivated GaAsP single-nanowire solar cells exceeding 10% efficiency grown on silicon. *Nature Communications*, **2013**, 4, 1498	17.4	168
15	Single-nanowire solar cells beyond the Shockley–Queisser limit. *Nature Photonics*, **2013**, 7, 306-310	33.9	607
14	Experimental determination of adatom diffusion lengths for growth of InAs nanowires. *Journal of Crystal Growth*, **2013**, 364, 16-22	1.6	37
13	Doping incorporation paths in catalyst-free Be-doped GaAs nanowires. *Applied Physics Letters*, **2013**, 102, 013117	3.4	55
12	Direct observation of interface and nanoscale compositional modulation in ternary III-As heterostructure nanowires. *Applied Physics Letters*, **2013**, 103, 063106	3.4	15

11	Electrical contacts to single nanowires: a scalable method allowing multiple devices on a chip. Application to a single nanowire radial p-i-n junction. *International Journal of Nanotechnology*, **2013**, 10, 419	1.5	8
10	Suppression of three dimensional twinning for a 100% yield of vertical GaAs nanowires on silicon. *Nanoscale*, **2012**, 4, 1486-90	7.7	68
9	An electrically-driven GaAs nanowire surface plasmon source. *Nano Letters*, **2012**, 12, 4943-7	11.5	55
8	In-situ x-ray characterization of wurtzite formation in GaAs nanowires. *Applied Physics Letters*, **2012**, 100, 093103	3.4	43
7	Influence of the oxide layer for growth of self-assisted InAs nanowires on Si(111). *Nanoscale Research Letters*, **2011**, 6, 516	5	27
6	Engineering light absorption in single-nanowire solar cells with metal nanoparticles. *New Journal of Physics*, **2011**, 13, 123026	2.9	23
5	Three-dimensional multiple-order twinning of self-catalyzed GaAs nanowires on Si substrates. *Nano Letters*, **2011**, 11, 3827-32	11.5	112
4	Impact of the liquid phase shape on the structure of III-V nanowires. *Physical Review Letters*, **2011**, 106, 125505	7.4	92
3	Structural phase control in self-catalyzed growth of GaAs nanowires on silicon (111). *Nano Letters*, **2010**, 10, 4475-82	11.5	188
2	Junctions in axial III-V heterostructure nanowires obtained via an interchange of group III elements. *Nano Letters*, **2009**, 9, 3689-93	11.5	79
1	Electronic Structure of InAs and InSb Surfaces: Density Functional Theory and Angle-Resolved Photoemission Spectroscopy. *Advanced Quantum Technologies*,2100033	4.3	1